



Session Title	[MoA2] OFET II
Date / Time	July 2 (Mon.), 2018 / 13:30-15:30
Room	Room A (#101+102)
Session Chair	TBA

MoA2-I1 (Invited)

13:30-13:55

Small-Molecule, Low-Voltage p-Channel and n-Channel Organic Thin-Film Transistors for Flexible Organic Circuits

Hagen Klauk

Max Planck Inst. for Solid State Research, Germany

MoA2-O2

13:55-14:10

Light-Emitting Field-Effect Transistors based on Polyfluorene – Cesium Lead Halide Nanocrystals Composite Films

Andrey Aleshin¹, Igor Shcherbakov¹, and Leo Matyushkin²

¹Ioffe Inst., Russia, ²St. Petersburg Electrotechnical Univ., Russia

MoA2-O3

14:10-14:25

FTM as A Highly Facile Method Towards Fabrication of Macroscopically Oriented Thin Films for Anisotropic Electronic Devices

Shyam S. Pandey, Manish Pandey, Atul Sm Tripathi, Shifumi Sadakata, Nikita Kumari, Shuichi Nagamtsu, and Shuzi Hayase

Kyushu Inst. of Tech., Japan

MoA2-O4

14:25-14:40

Removing The Current-Limit of Vertical Organic Field Effect Transistors

Nir Tessler and Gil Sheleg

Technion, Israel

MoA2-O5

14:40-14:55

3D Integration of Printed Organic Dual-Gate FETs on A Flexible Substrate

Jimin Kwon¹, Sungjune Jung¹, Kilwon Cho¹, Shizuo Tokito², Yasunori Takeda², and Rei Shiwaku²

¹POSTECH, Korea, ²Yamagata Univ., Japan

MoA2-I6 (Invited)

14:55-15:20

Ion Gel-Gated Vertical Graphene Schottky Barrier Transistors on Plastic

Jeong Ho Cho

Sungkyunkwan Univ., Korea